



IRL640A

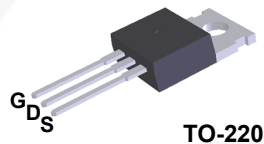
N-Channel Logic Level A-FET 200 V, 18 A, 180 mΩ

Description

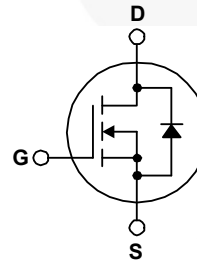
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, DC-AC converters for uninterrupted power supply and motor control.

Features

- 18 A, 200 V, $R_{DS(on)} = 180 \text{ m}\Omega @ V_{GS} = 5 \text{ V}$
- Low Gate Charge (Typ. 40 nC)
- Low Crss (Typ. 95 pF)
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability
- Logic-Level Gate Drive



TO-220



Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	200	V
I_D	Continuous Drain Current ($T_C=25^\circ\text{C}$)	18	A
	Continuous Drain Current ($T_C=100^\circ\text{C}$)	11.4	
I_{DM}	Drain Current-Pulsed (1)	63	A
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (2)	64	mJ
I_{AR}	Avalanche Current (1)	18	A
E_{AR}	Repetitive Avalanche Energy (1)	11	mJ
dv/dt	Peak Diode Recovery dv/dt (3)	5	V/ns
P_D	Total Power Dissipation ($T_C=25^\circ\text{C}$)	110	W
	Linear Derating Factor	0.88	
T_J, T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8. from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.14	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Case-to-Sink	0.5	--	
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
IRL640A	IRL640A	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	200	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.17	--	V/ $^\circ\text{C}$	$I_D=250\mu A$ See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	1.0	--	2.0	V	$V_{DS}=5V, I_D=250\mu A$
I_{GSS}	Gate-Source Leakage, Forward	--	--	100	nA	$V_{GS}=20V$
	Gate-Source Leakage, Reverse	--	--	-100		$V_{GS}=-20V$
I_{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	$V_{DS}=200V$
		--	--	100		$V_{DS}=160V, T_C=125^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.18	Ω	$V_{GS}=5V, I_D=9A$ (4)
g_{fs}	Forward Transconductance	--	13.3	--	\bar{S}	$V_{DS}=40V, I_D=9A$ (4)
C_{iss}	Input Capacitance	--	1310	1705	pF	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$ See Fig 5
C_{oss}	Output Capacitance	--	200	250		
C_{rss}	Reverse Transfer Capacitance	--	95	120		
$t_{d(on)}$	Turn-On Delay Time	--	11	30		
t_r	Rise Time	--	8	25	ns	$V_{DD}=100V, I_D=18A,$ $R_G=4.6\Omega$ See Fig 13 (4) (5)
$t_{d(off)}$	Turn-Off Delay Time	--	46	100		
t_f	Fall Time	--	15	40		
Q_g	Total Gate Charge	--	40	56	nC	$V_{DS}=160V, V_{GS}=5V,$ $I_D=18A$ See Fig 6 & Fig 12 (4) (5)
Q_{gs}	Gate-Source Charge	--	6.8	--		
Q_{gd}	Gate-Drain (. Miller.) Charge	--	18.6	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	18	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current (1)	--	--	63		
V_{SD}	Diode Forward Voltage (4)	--	--	1.5	V	$T_J=25^\circ\text{C}, I_S=18A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	--	224	--	ns	$T_J=25^\circ\text{C}, I_F=18A$
Q_{rr}	Reverse Recovery Charge	--	1.55	--	μC	$di_F/dt=100A/\mu\text{s}$ (4)

Notes;

- (1) Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- (2) $L=0.3\text{mH}, I_{AS}=18A, V_{DD}=50V, R_G=27\Omega,$ Starting $T_J=25^\circ\text{C}$
- (3) $I_{SD} \leq 18A, di/dt \leq 260A/\mu\text{s}, V_{DD} \leq BV_{DSS},$ Starting $T_J=25^\circ\text{C}$
- (4) Pulse Test: Pulse Width = $250\mu\text{s},$ Duty Cycle $\leq 2\%$
- (5) Essentially Independent of Operating Temperature

Typical Characteristics

Fig 1. Output Characteristics

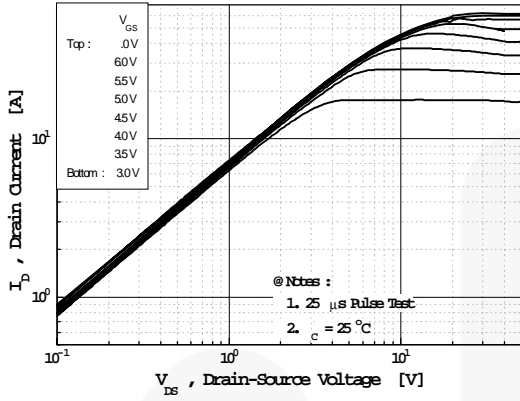


Fig 2. Transfer Characteristics

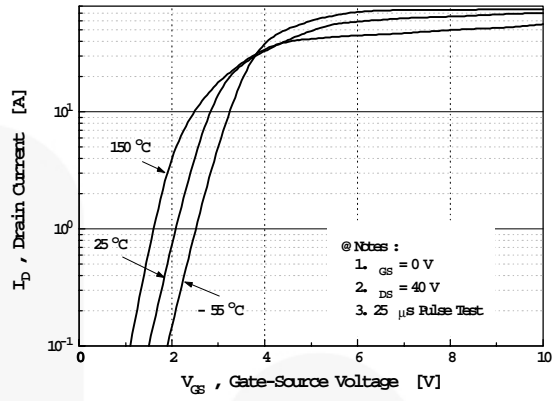


Fig 3. On-Resistance vs. Drain Current

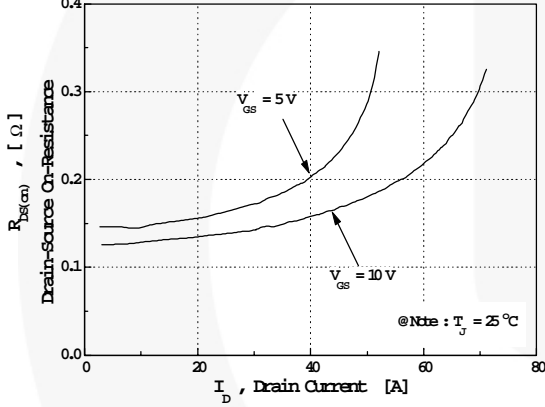


Fig 4. Source-Drain Diode Forward Voltage

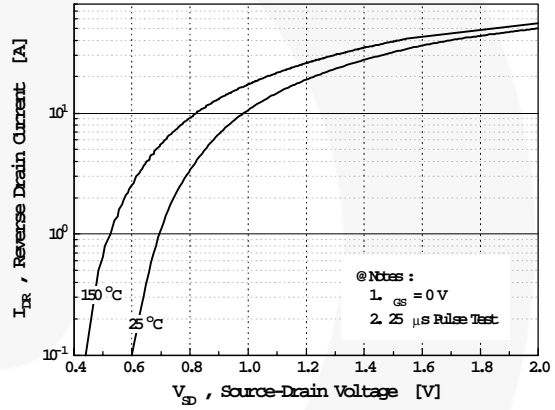


Fig 5. Capacitance vs. Drain-Source Voltage

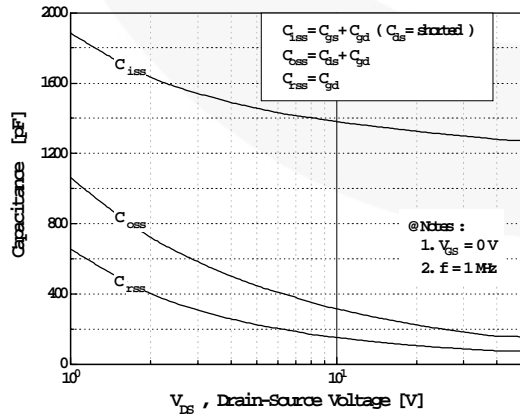
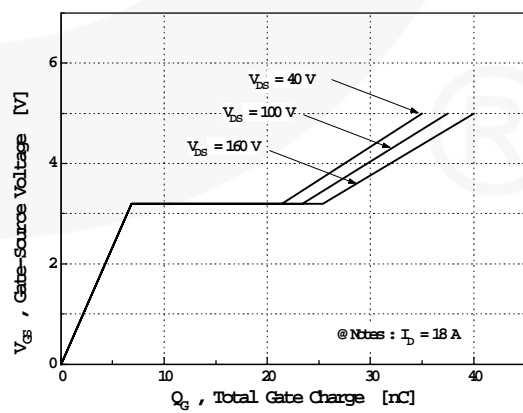


Fig 6. Gate Charge vs. Gate-Source Voltage



Typical Characteristics (continued)

Fig 7. Breakdown Voltage vs. Temperature

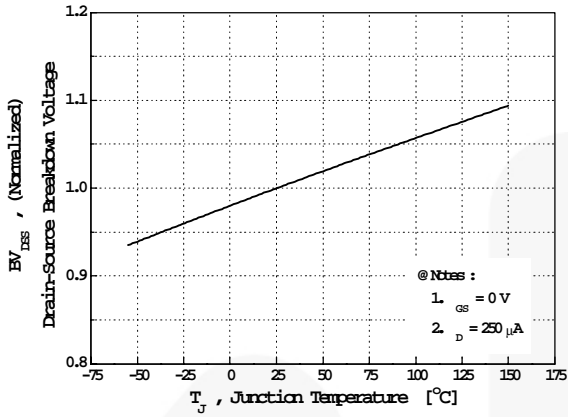


Fig 8. On-Resistance vs. Temperature

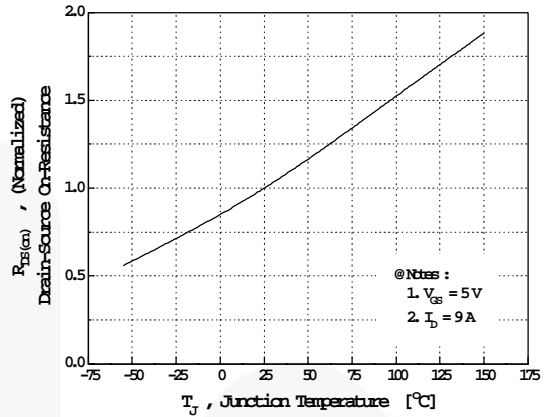


Fig 9. Max. Safe Operating Area

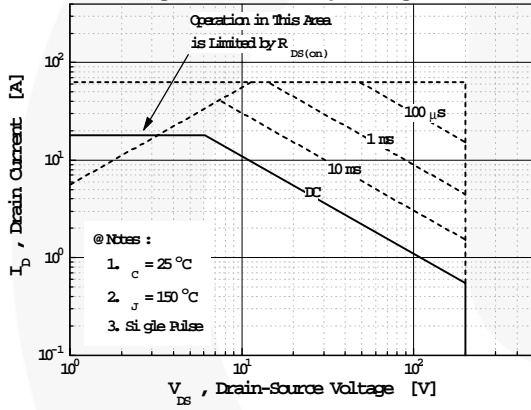


Fig 10. Max. Drain Current vs. Case Temperature

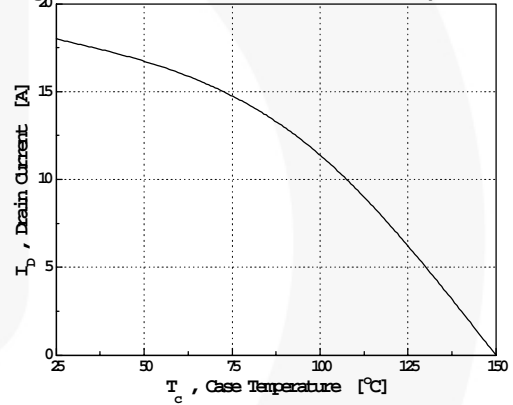
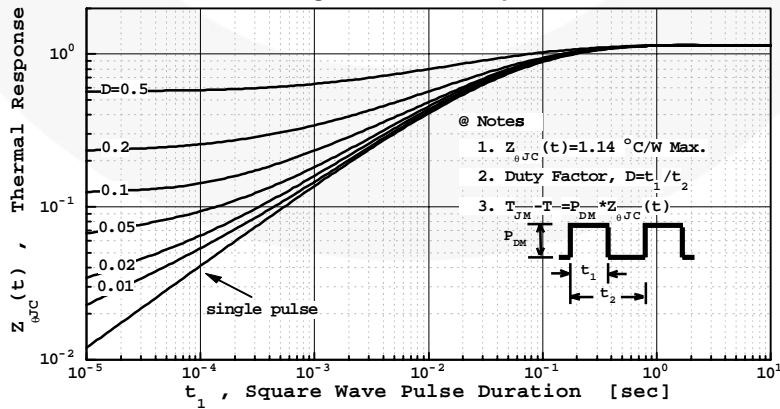


Fig 11. Thermal Response



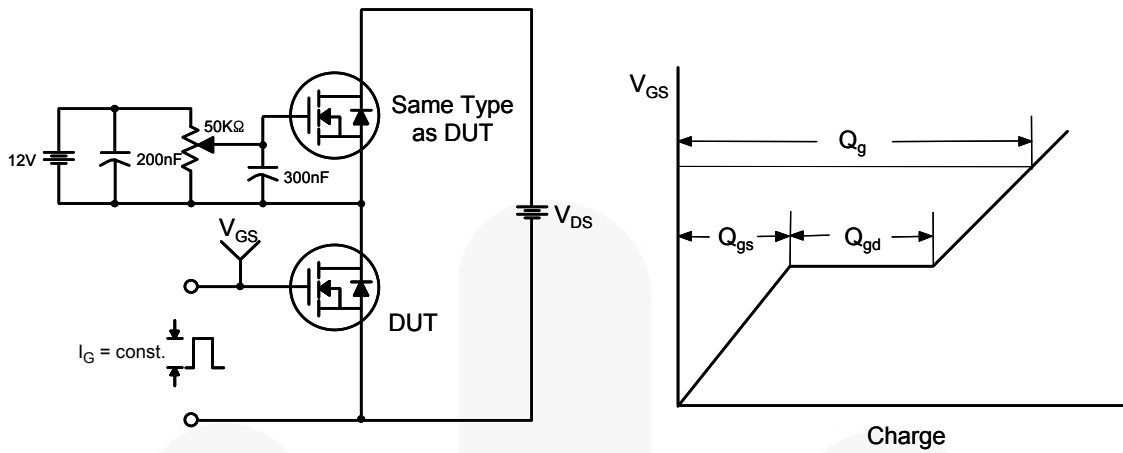


Figure 12. Gate Charge Test Circuit & Waveform



Figure 13. Resistive Switching Test Circuit & Waveforms

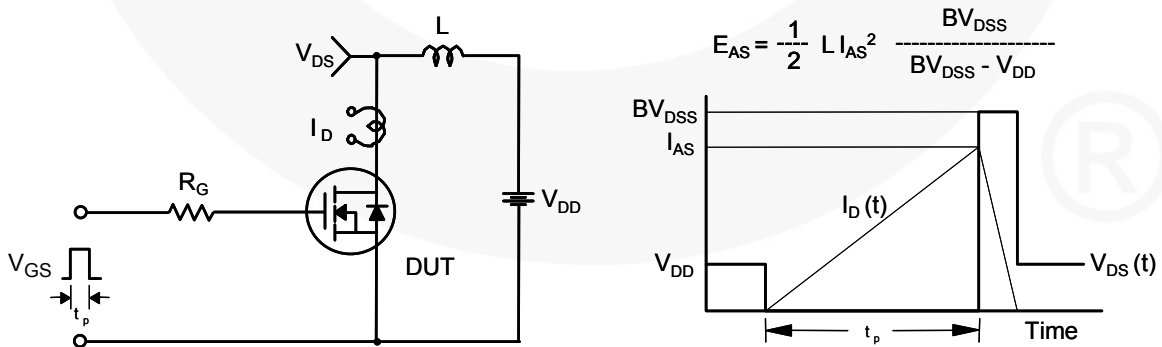


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

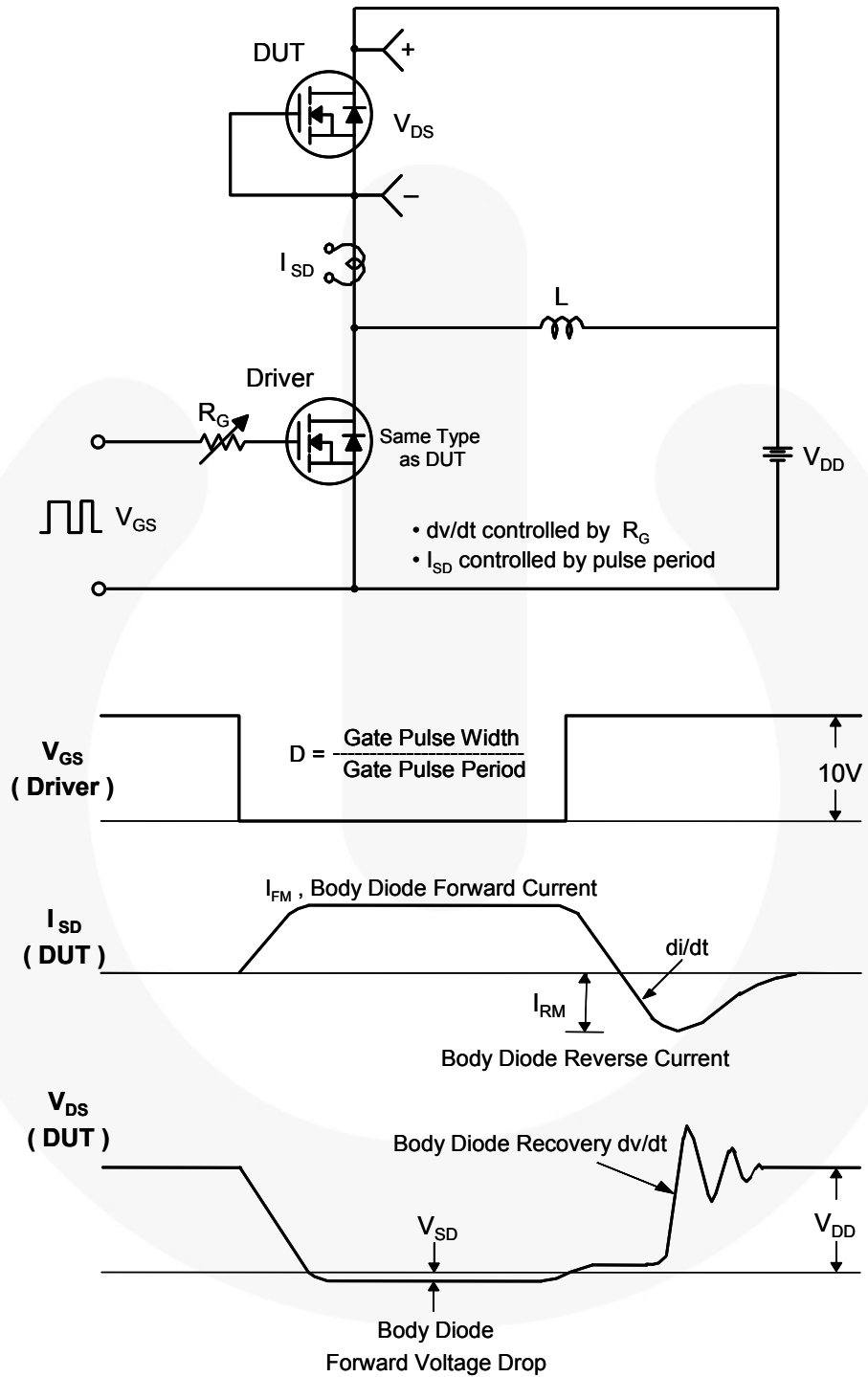
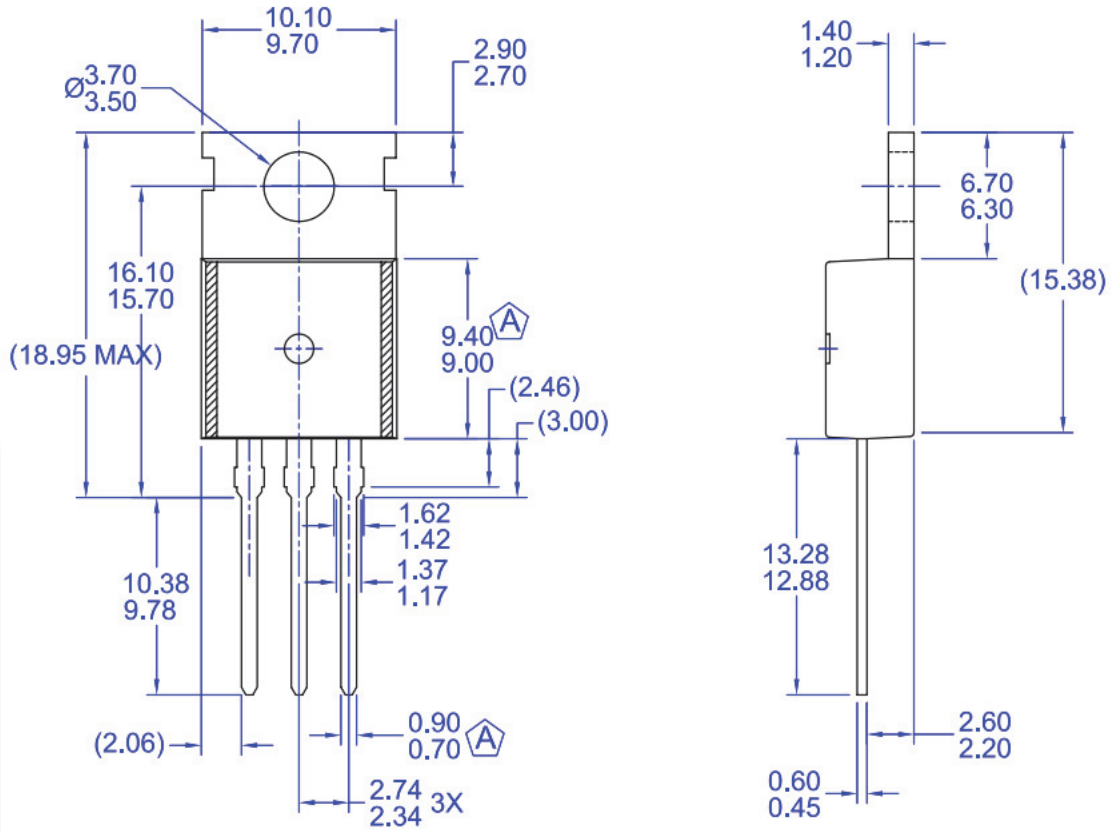


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES:

- A) CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED
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- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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